

## Silicon Epitaxial Planar Switching Diode

### Features

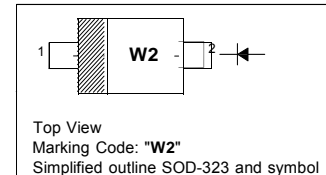
- Low forward voltage
- Fast Reverse Recovery Time
- Small Total Capacitance

### Application

- Ultra high speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	$V_{RM}$	85	V
Reverse Voltage	$V_R$	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	$I_{FM}$	200	mA
Surge Forward Current (10 ms)	$I_{FSM}$	1	A
Power Dissipation	$P_{tot}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	$V_F$	1.2	V
Reverse Current at $V_R = 30\text{ V}$ at $V_R = 80\text{ V}$	$I_R$	0.1 0.5	$\mu\text{A}$
Total Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	3	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$ , $V_R = 6\text{ V}$ , $R_L = 100\ \Omega$	$t_{rr}$	4	ns

